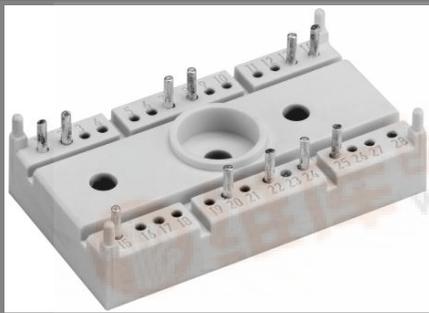


SK 55 GARL 065 E



SEMITOP® 3

IGBT Module

SK 55 GARL 065 E

Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N-channel homogeneous silicon structure (NPT-Non punch-through IGBT)
- High short circuit capability
- Low tail current with low temperature dependence

Typical Applications

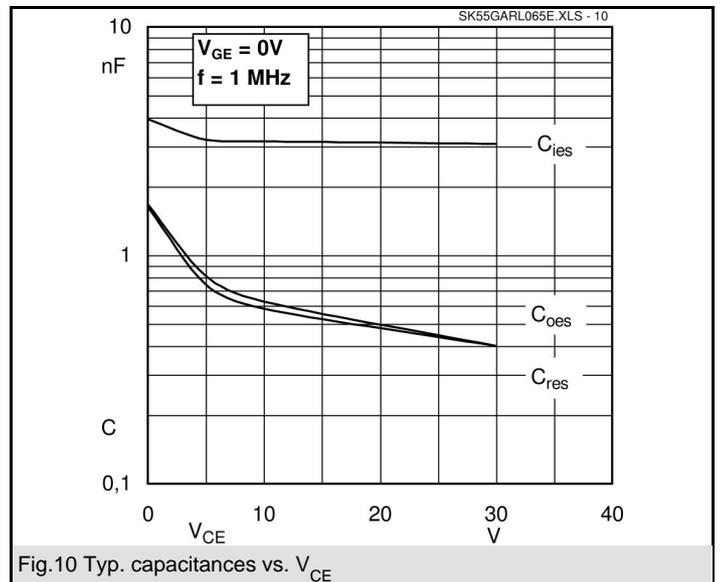
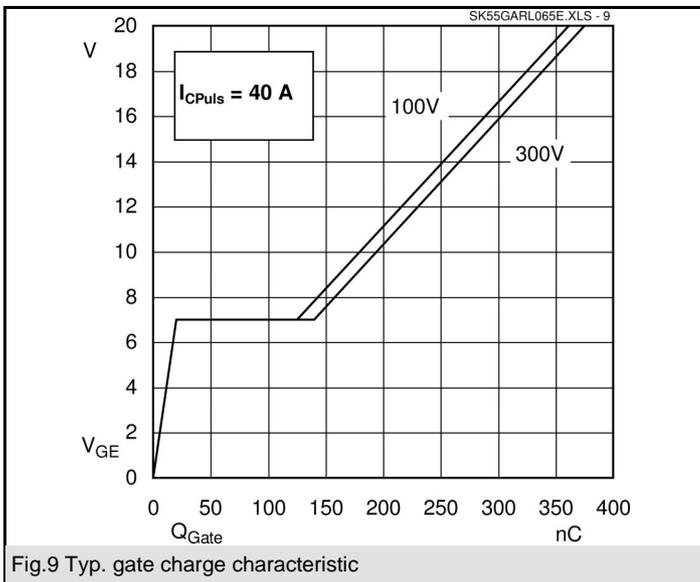
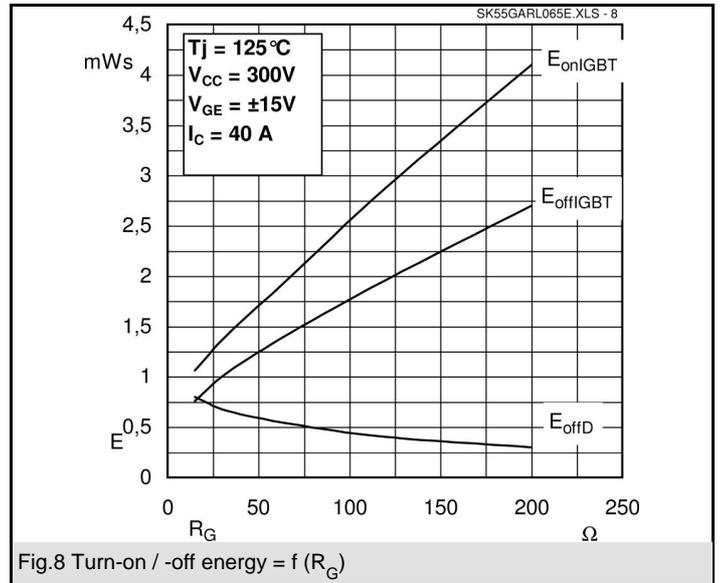
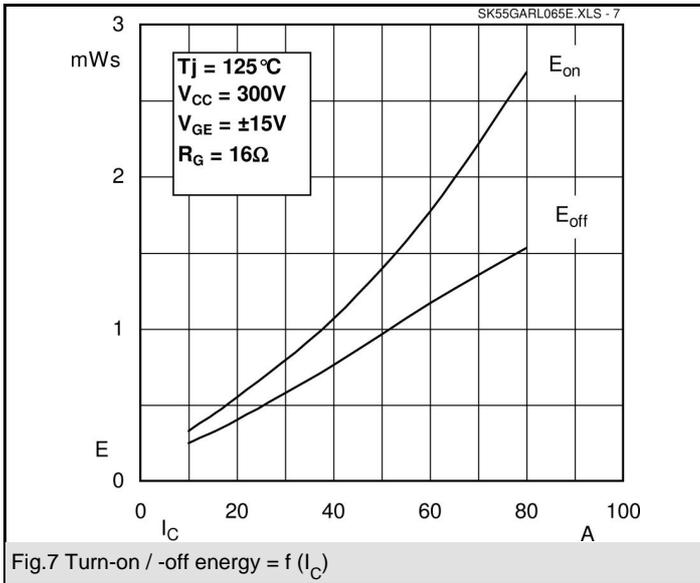
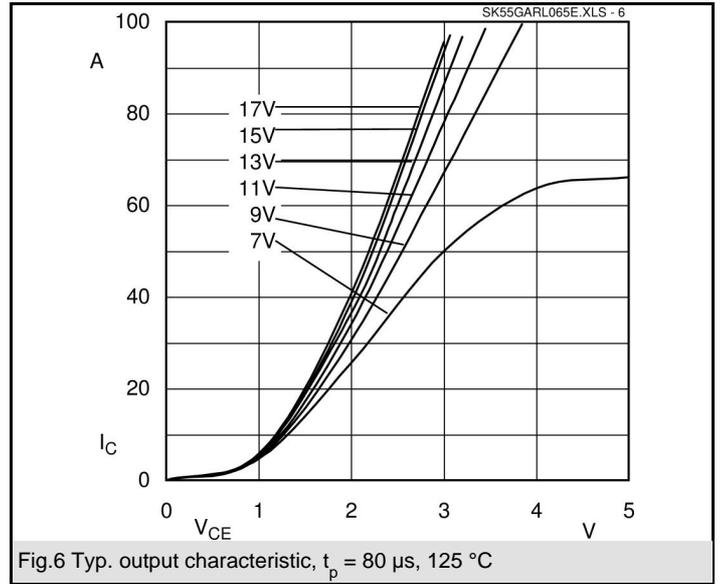
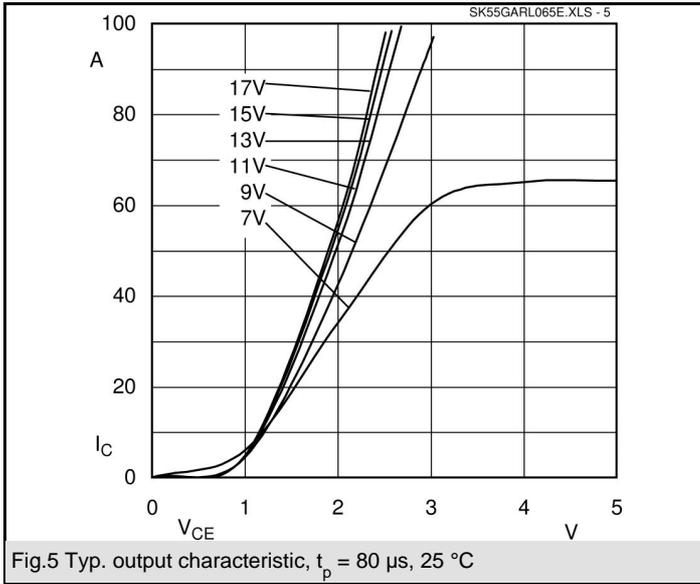
- Switching (not for linear use)
- Switched mode power supplies
- UPS
- Double PFC
- Multilevel Inverter

Absolute Maximum Ratings		$T_s = 25\text{ }^\circ\text{C}$, unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}		600		V
V_{GES}		± 20		V
I_C	$T_s = 25\text{ (80) }^\circ\text{C}$;	54 (40)		A
I_{CM}	$t_p < 1\text{ ms}$; $T_s = 25\text{ (80) }^\circ\text{C}$;	108 (80)		A
T_j		- 40 ... + 150		$^\circ\text{C}$
Freewheeling CAL diode				
I_F	$T_s = 25\text{ (80) }^\circ\text{C}$;	64 (48)		A
$I_{FM} = -I_{CM}$	$t_p < 1\text{ ms}$; $T_s = 25\text{ (80) }^\circ\text{C}$;	124 (96)		A
T_j		- 40 ... + 150		$^\circ\text{C}$
T_{stg}		- 40 ... + 125		$^\circ\text{C}$
T_{sol}	Terminals, 10 s	260		$^\circ\text{C}$
V_{isol}	AC 50 Hz, r.m.s. 1 min. / 1 s	2500 / 3000		V

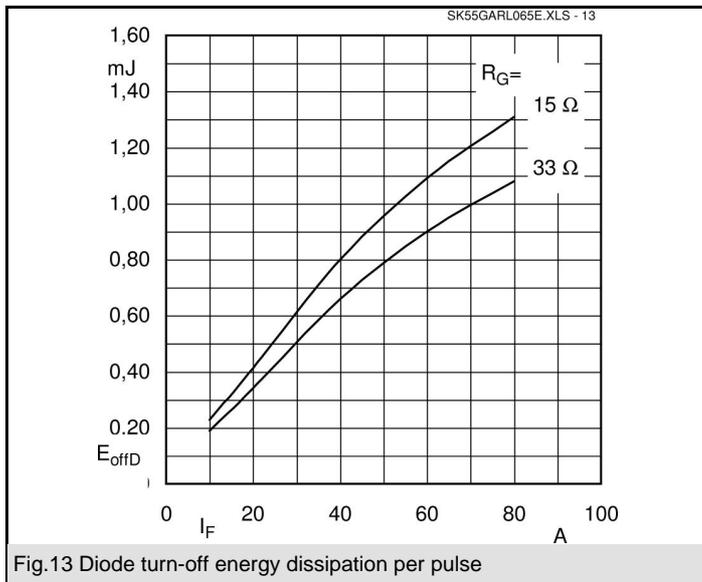
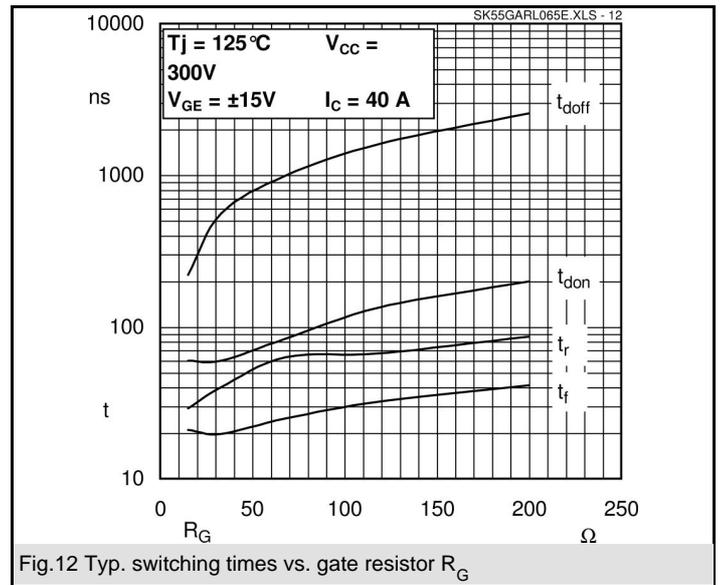
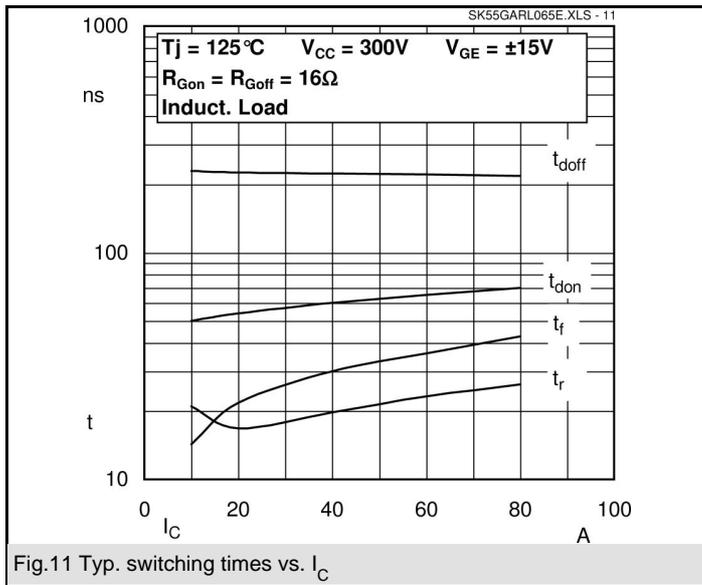
Characteristics		$T_s = 25\text{ }^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{CE(sat)}$	$I_C = 40\text{ A}$, $T_j = 25\text{ (125) }^\circ\text{C}$		1,7 (2,2)	2 (2,2)	V
$V_{GE(th)}$	$V_{CE} = V_{GE}$; $I_C = 0,0014\text{ A}$	4,5	5,5	6,5	V
C_{ies}	$V_{CE} = 25\text{ V}$; $V_{GE} = 0\text{ V}$; 1 MHz		3		nF
$R_{th(j-s)}$	per IGBT per module			0,85	K/W K/W
under following conditions:					
$t_{d(on)}$	$V_{CC} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$		60	80	ns
t_r	$I_C = 40\text{ A}$, $T_j = 125\text{ }^\circ\text{C}$		30	40	ns
$t_{d(off)}$	$R_{Gon} = R_{Goff} = 16\text{ }\Omega$		220	280	ns
t_f			20	26	ns
$E_{on} + E_{off}$	Inductive load		1,8		mJ
Freewheeling CAL diode					
$V_F = V_{EC}$	$I_F = 50\text{ A}$; $T_j = 25\text{ (125) }^\circ\text{C}$		1,45 (1,4)	1,7 (1,75)	V
$V_{(TO)}$	$T_j = 125\text{ }^\circ\text{C}$		0,85	0,9	V
r_T	$T_j = 125\text{ () }^\circ\text{C}$		11	16	m Ω
$R_{th(j-s)}$				1,1	K/W
under following conditions:					
I_{RRM}	$I_F = 50\text{ A}$; $V_R = 300\text{ V}$		30		A
Q_{rr}	$di_F/dt = -800\text{ A}/\mu\text{s}$		3,6		μC
E_{off}	$V_{GE} = 0\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$		0,95		mJ
Mechanical data					
M1	mounting torque			2,5	Nm
w			30		g
Case	SEMITOP® 3		T55		



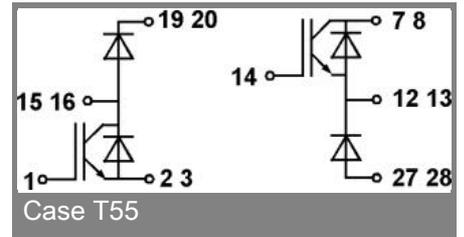
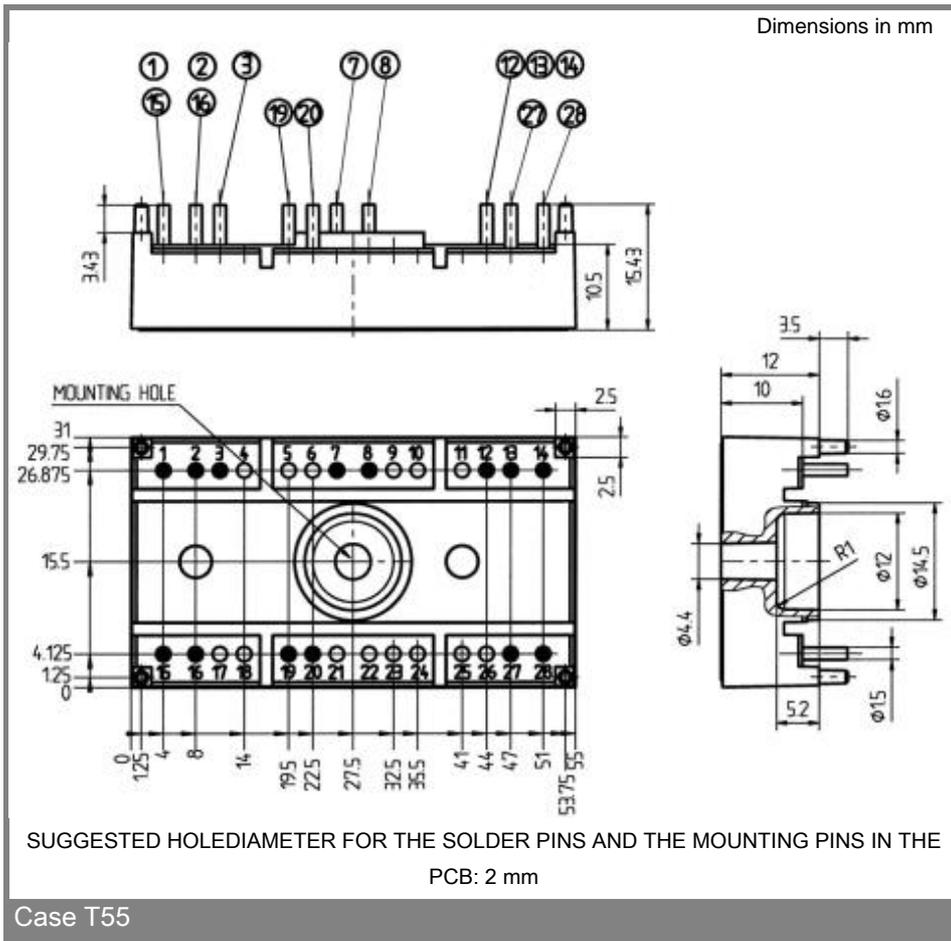
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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.